NSN 5961-01-023-1697

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View Online at https://aerobasegroup.com/nsn/5961-01-023-1697 **Inclosure Material:** Metal all transistor **Overall Length:** 1.573 inches all transistor **Overall Height:** 0.350 inches all transistor Overall Width: 1.050 inches all transistor **Mounting Facility Quantity:** 2 all transistor **Internal Configuration:** Junction contact all transistor Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 all transistor **Electrode Internally-electrically Connected To Case:** Collector all transistor **Internal Junction Configuration:** Pnp all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole all transistor **Semiconductor Material:** Germanium all transistor Voltage Rating In Volts Per Characteristic: 50.0 breakdown voltage, collector-to-emitter, base open all transistor and 75.0 breakdown voltage, collector-to-base, emitter open all transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor **Current Rating Per Characteristic:** 11.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 40.0 watts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 110.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 2 pin all transistor and 1 case all transistor Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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